



Description

The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP2G86 is a dual two-input EXCLUSIVE OR gate. Both gates have push-pull outputs designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down. Each gate performs the positive Boolean function:

$$Y = A \oplus B \text{ or } Y = \overline{A}B + A\overline{B}$$

Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static Power Consumption $I_{CC} < 0.9 \mu A \label{eq:local_$
- Low Dynamic Power Consumption C_{PD} = 6 pF (Typical at 3.6V)
- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250 mV at V_{CC} = 3.0V
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22 2000-V Human Body Model (A114) Exceeds 1000-V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments



Applications

- Suited for Battery and Low Power Needs
- Wide array of products such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation/GPS
 - MP3 Players, Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks
 - Computer Peripherals, Hard Drives, SSD, CD/DVD ROM
 - TV, DVD, DVR, Set-Top Box

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





	Package Package Package Package	Package	7" Tape and	d Reel	
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74AUP2G86RA3-7	RA3	X2-DFN1210-8	1.2mm x 1.0mm x 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Pin	Function
1A	1	Data Input
1B	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
2B	6	Data Input
1Y	7	Data Output
V _{CC}	8	Supply Voltage

Logic Diagram



Function Table

Inp	outs	Output
Α	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L



Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI<0	50	mA
loк	Output Clamp Current (V _O < 0)	50	mA
Ιο	Continuous Output Current ($V_O = 0$ to V_{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8)

Symbol	Pa	arameter	Min	Max	Unit	
V _{CC}	Operating Voltage	_	0.8	3.6	V	
VI	Input Voltage		0	3.6	V	
Vo	Output Voltage	0	V _{CC}	V		
		V _{CC} = 0.8V	—	-20	μA	
		V _{CC} = 1.1V	—	-1.1		
	I _{OH} High-Level Output Current	V _{CC} = 1.4V	—	-1.7		
IOH	High-Level Output Current	V _{CC} = 1.65V	—	-1.9	mA	
		V _{CC} = 2.3V	—	-3.1		
		V _{CC} = 3.0V	—	-4		
		V _{CC} = 0.8V	—	20	μA	
		V _{CC} = 1.1V	—	1.1		
		V _{CC} = 1.4V	—	1.7		
I _{OL}	Low-Level Output Current	V _{CC} = 1.65V	—	1.9	mA	
		V _{CC} = 2.3V	_	3.1		
		V _{CC} = 3.0V	—	4	1	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	—	200	ns/V	
TA	Operating Free-Air Temperature	_	-40	+125	°C	

Note: 8. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics

Symbol	Deremeter	Test Conditions	V	T _A = -	+25°C	T _A = -40°0	C to +85°C	Unit
Symbol	Parameter	Test Conditions	V _{CC}	Min	Max	Min	Max	Unit
		_	0.8V to 1.65V	0.80 x V _{CC}	—	0.80 x V _{CC}	—	
V	High-Level Input	_	1.65V to 1.95V	0.65 x V _{CC}	—	0.65 x V _{CC}	—	v
VIH	Voltage	_	2.3V to 2.7V	1.6	—	1.6	—	
		_	3.0V to 3.6V	2.0	—	2.0	—	
			0.8V to 1.65V	—	$0.30 \times V_{CC}$	—	$0.30 \times V_{CC}$	
VIL	Low-Level Input		1.65V to 1.95V	—	$0.35 \times V_{CC}$	—	$0.35 \times V_{CC}$	V
۷IL	Voltage		2.3V to 2.7V	—	0.7	—	0.7	v
			3.0V to 3.6V		0.9		0.9	
		I _{OH} = -20µА	0.8V to 3.6V	V _{CC} -0.1	—	V _{CC} -0.1	—	
		I _{OH} = -1.1mA	1.1V	$0.75 \times V_{CC}$	—	$0.7 \times V_{CC}$	—	
		I _{OH} = -1.7mA	1.4V	1.11	—	1.03	—	
	High-Level Output	I _{OH} = -1.9mA	1.65V	1.32	—	1.3	—	
Voh	VOH Voltage	I _{OH} = -2.3mA	0.01/	2.05	_	1.97	—	V
		I _{OH} = -3.1mA	2.3V	1.9	—	1.85	—	
		I _{OH} = -2.7mA	0)/	2.72	_	2.67	_	
		I _{OH} = -4mA	- 3V	2.6	_	2.55	_	
		I _{OL} = 20μΑ	0.8V to 3.6V	_	0.1	_	0.1	
		I _{OL} = 1.1mA	1.1V	_	0.3 x V _{CC}	_	0.3 x V _{CC}	
		I _{OL} = 1.7mA	1.4V		0.31		0.37	
	Low-Level Input	I _{OL} = 1.9mA	1.65V	_	0.31	_	0.35	
Vol	Voltage	I _{OL} = 2.3mA	0.01/	_	0.31	_	0.33	V
		I _{OL} = 3.1mA	- 2.3V	_	0.44	—	0.45	
		I _{OL} = 2.7mA		—	0.31	—	0.33	
		I _{OL} = 4mA	- 3V	_	0.44	_	0.45	
I _I	Input Current	A or B Input VI = GND to 3.6V	0V to 3.6V	_	± 0.1	_	± 0.5	μΑ
I _{OFF}	Power Down Leakage Current	$V_{I} \text{ or } V_{O} = 0V \text{ to } 3.6V$	0V	_	± 0.2	_	± 0.6	μA
Δl _{OFF}	Delta Power Down Leakage Current	$V_1 \text{ or } V_0 = 0V \text{ to } 3.6V$	0V to 0.2V	_	± 0.2	_	± 0.6	μA
Icc	Supply Current	$V_{I} = GND \text{ or } V_{CC}, I_{O} = 0$	0.8V to 3.6V	—	0.5	—	0.9	μA
ΔI _{CC}	Additional Supply Current	One Input at V_{CC} –0.6V Other Inputs at V_{CC} or GND	3.3V	_	40	_	50	μA



Electrical Characteristics (continued)

Symbol	Parameter	Test Conditions	V _{cc}	T _A = -40°C	to +125°C	Unit	
Symbol	Falanielei	Test conditions	VCC	Min	Max	onit	
		_	0.8V to 1.65V	0.80 x V _{CC}	—		
VIH	High-Level Input Voltage	—	1.65V to 1.95V	0.70 x V _{CC}	—	V	
VIH			2.3V to 2.7V	1.6	—	v	
		—	3.0V to 3.6V	2.0			
		_	0.8V to 1.65V		0.25 x V _{CC}		
VIL	Low-Level Input Voltage	_	1.65V to 1.95V	—	0.30 x V _{CC}	V	
۷IL	Low Level input voltage	_	2.3V to 2.7V	—	0.7	v	
			3.0V to 3.6V	_	0.9		
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} – 0.11			
		I _{OH} = -1.1mA	1.1V	$0.6 \times V_{CC}$	—		
		I _{OH} = -1.7mA	1.4V	0.93	—		
	Llink Lough Output) (altana	I _{OH} = -1.9mA	1.65V	1.17	—	V	
V _{OH} H	High-Level Output Voltage	I _{OH} = -2.3mA	0.01/	1.77	—	V	
		I _{OH} = -3.1mA	2.3V	1.67			
		I _{OH} = -2.7mA	2) (2.40			
		I _{OH} = -4mA	- 3V	2.30			
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11		
		I _{OL} = 1.1mA	1.1V	_	0.33 x V _{CC}		
		I _{OL} = 1.7mA	1.4V	_	0.41		
.,		I _{OL} = 1.9mA	1.65V	_	0.39		
V _{OL}	Low-Level Input Voltage	I _{OL} = 2.3mA	0.01/	_	0.36	V	
		I _{OL} = 3.1mA	2.3V	_	0.50		
		I _{OL} = 2.7mA	a) /	_	0.36		
		I _{OL} = 4mA	3V		0.50		
h	Input Current	A or B Input, V_1 = GND to 3.6V	0V to 3.6V	_	± 0.75	μA	
IOFF	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V	_	± 1.0	μA	
ΔI _{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA	
Icc	Supply Current	$V_{I} = GND \text{ or } V_{CC}, I_{O} = 0$	0.8V to 3.6V	_	3.0	μA	
ΔI _{CC}	Additional Supply Current	Input at $V_{CC} = -0.6V$ Other Inputs at V_{CC} or GND	3.3V		75	μA	

Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

	Parameter	Te: Condi		V _{cc}	Тур	Unit
				0.8V	5.1	
				1.2V ± 0.1V	5.2	
0	Power Dissipation	f = 1N	ЛНz	1.5V ± 0.1V	5.2	
C _{pd}	Capacitance	No L	oad	1.8V ± 0.15V	5.5	pF
				2.5V ± 0.2V	5.7	
				3.3V ± 0.3V	6.0	
Ci	Input Capacitance	V _i = V _{CC}	or GND	0V or 3.3V	2.0	pF
θ_{JA}	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8	(Note 9)	—	+395	°C/W
θ _{JC}	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	—	+236	°C/W

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

C_L = 5pF, See Figure 1

Parameter	From	To Output	V _{cc}	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Faranieter	Input			Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	24.4	_	_	_	_	_	
		Y	1.2V ± 0.1V	2.3	5.9	14.4	2.1	15.3	2.1	16.6	
	A or B		1.5V ± 0.1V	1.8	4.1	7.7	1.6	8.8	1.6	9.7	20
t _{pd}	AUD		1.8V ± 0.15V	1.5	3.3	5.9	1.4	6.9	1.4	7.6	ns
			2.5V ± 0.2V	1.2	2.6	4.4	1.1	5.3	1.1	5.9	
			3.3V ± 0.3V	1.0	2.3	4.0	0.9	4.7	0.9	5.2	

C_L = 10p, See Figure 1

Parameter	From	To Output	v _{cc}	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C	Unit	
Inp	Input			Min	Тур	Max	Min	Max	Min	Max	onn
			0.8V	_	28.4	-	—	_	_	_	- ns
		Y	1.2V ± 0.1V	2.6	6.8	16.3	2.4	17.3	2.4	18.8	
	A or D		1.5V ± 0.1V	2.2	4.8	8.7	1.9	10.0	1.9	11.0	
t _{pd} A or B	AOID		1.8V ± 0.15V	1.8	3.9	6.7	1.7	8.0	1.7	8.8	
			2.5V ± 0.2V	1.5	3.1	5.2	1.4	6.2	1.4	6.9	
			3.3V ± 0.3V	1.3	2.9	4.8	1.3	5.6	1.3	6.2	

C_L = 15pF, See Figure 1

Parameter	From	То	N	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Inpu	Input	Output	Vcc	Min	Тур	Max	Min	Max	Min	Max	Onit
			0.8V	_	32.4	_	—	—	_	_	ns
			1.2V ± 0.1V	3.0	7.6	18.2	2.7	19.4	2.7	21.0	
	A or B	v	1.5V ± 0.1V	2.4	5.3	9.6	2.2	11.3	2.2	12.5	
t _{pd}	AUID	T	1.8V ± 0.15V	2.1	4.4	7.5	1.9	9.0	1.9	9.9	
			2.5V ± 0.2V	1.8	3.6	5.9	1.6	7.0	1.6	7.7	
			3.3V ± 0.3V	1.4	3.3	5.4	1.4	6.4	1.4	7.1	

C_L = 30pF, See Figure 1

Parameter	From	То	N	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Input	Input	Output	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	44.3	-	_	—	-	_	
		1.2V ± 0.1V	3.9	9.9	23.7	3.5	25.8	3.5	27.9		
	A or B	Y	1.5V ± 0.1V	3.2	6.9	12.5	2.8	14.8	2.8	16.3	- ns
t _{pd}	AUID		1.8V ± 0.15V	2.8	5.7	9.8	2.5	11.7	2.5	12.9	
			2.5V ± 0.2V	2.4	4.7	7.6	2.2	9.1	2.2	10.1	
			3.3V ± 0.3V	1.9	4.4	7.1	1.8	8.3	1.8	9.2	



Parameter Measurement Information



Vcc	Inputs			•
	VI	t _r /t _f	V _M	CL
0.8V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ± 0.15V	Vcc	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V ± 0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V ± 0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF







Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied a pulse repetition rate ≤ 10 MHz.
 C. Inputs are measured separately one transition per measurement.

D. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$



Marking Information

X2-DFN1210-8



Part Number	Package	Identification Code	
74AUP2G86RA3-7	X2-DFN1210-8	FT	

X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.





X2-DFN1210-8				
Dim	Min	Max	Тур	
Α	-	0.35	0.30	
A1	0	0.03	0.02	
b	0.10	0.20	0.15	
D	1.15	1.25	1.20	
Е	0.95	1.05	1.00	
е	-	-	0.30	
К	-	-	0.25	
K 1	-	-	0.20	
L	0.25	0.35	0.30	
L1	0.30	0.40	0.35	
Z	0.050	0.100	0.075	
Z1	0.050	0.100	0.075	
All Dimensions in mm				

Dimensions	Value (in mm)	
С	0.300	
G	0.150	
Х	0.150	
X1	1.050	
Y	0.500	
Y1	1.150	



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